



YJG220G06AR

RECOMMEND
[YJG210G06AR](#)
FOR NEW DESIGN

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}

60V



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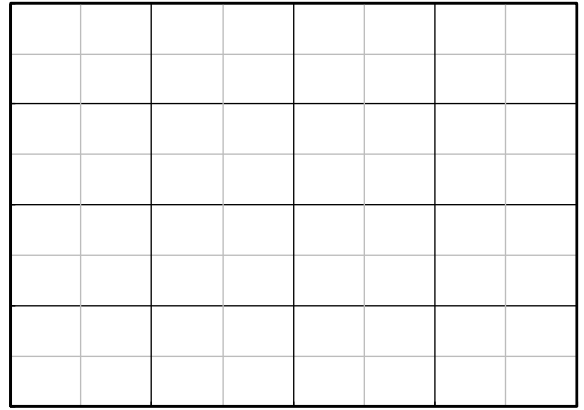
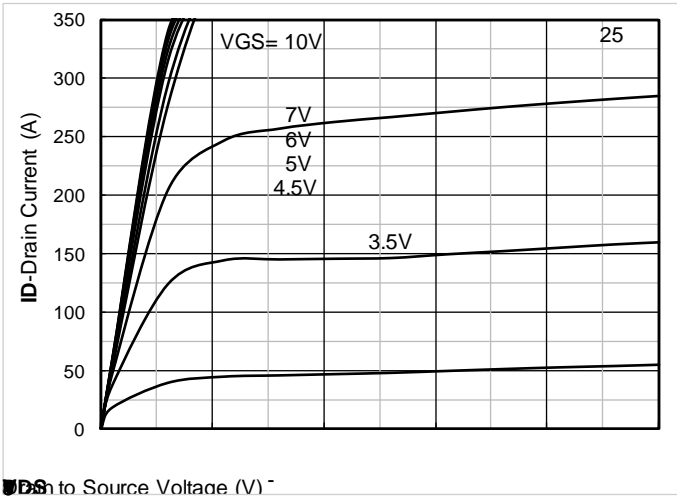
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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V



Typical Electrical and Thermal Characteristics Diagrams



Figure

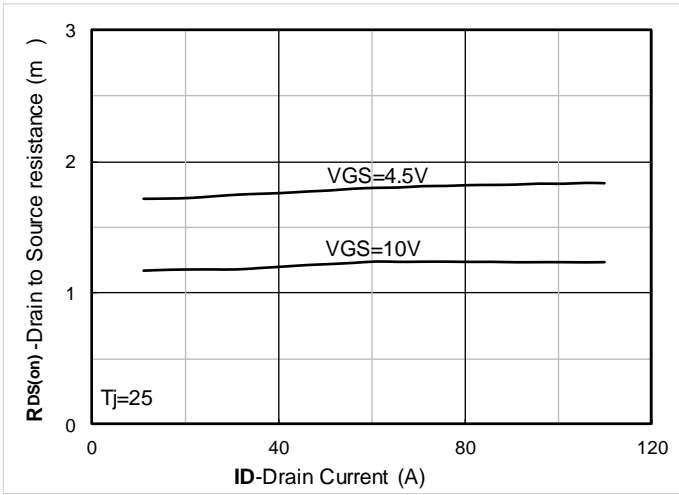


Figure 7. $R_{DS(on)}$ vs Drain Current

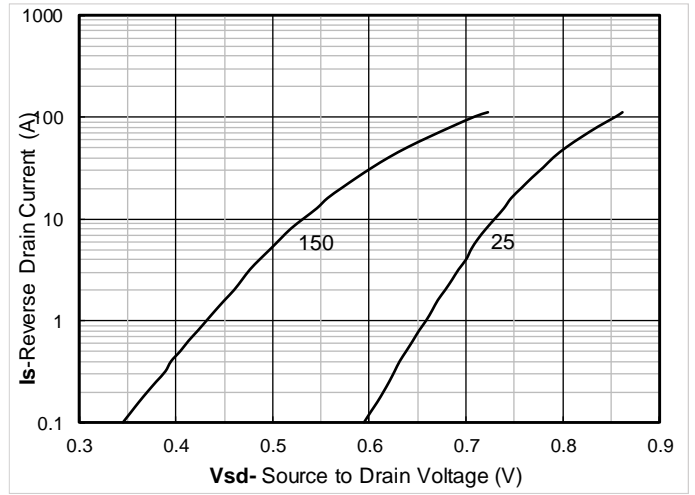


Figure 8. Forward characteristics of reverse diode



Figure 9. Normalized breakdown voltage



Figure 10. Normalized Threshold voltage

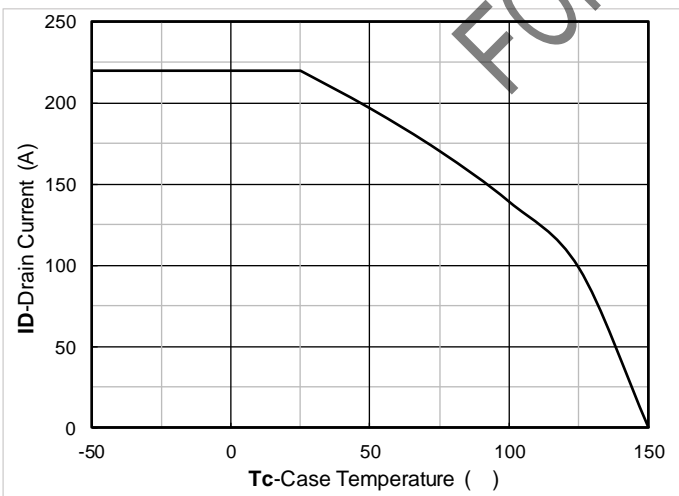


Figure 11. Current dissipation

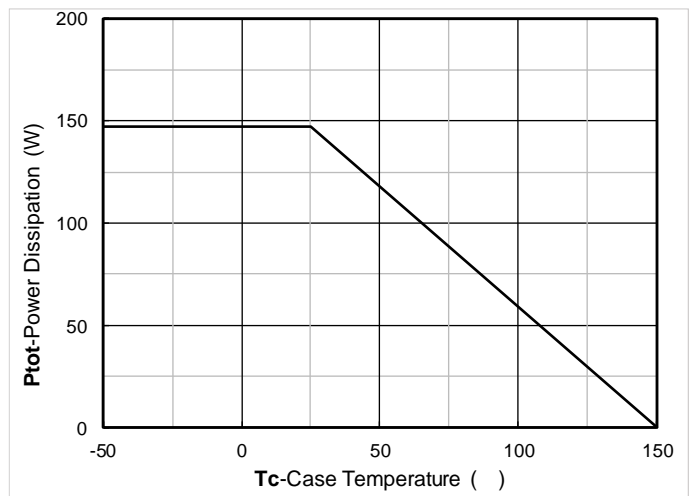


Figure 12. Power dissipation

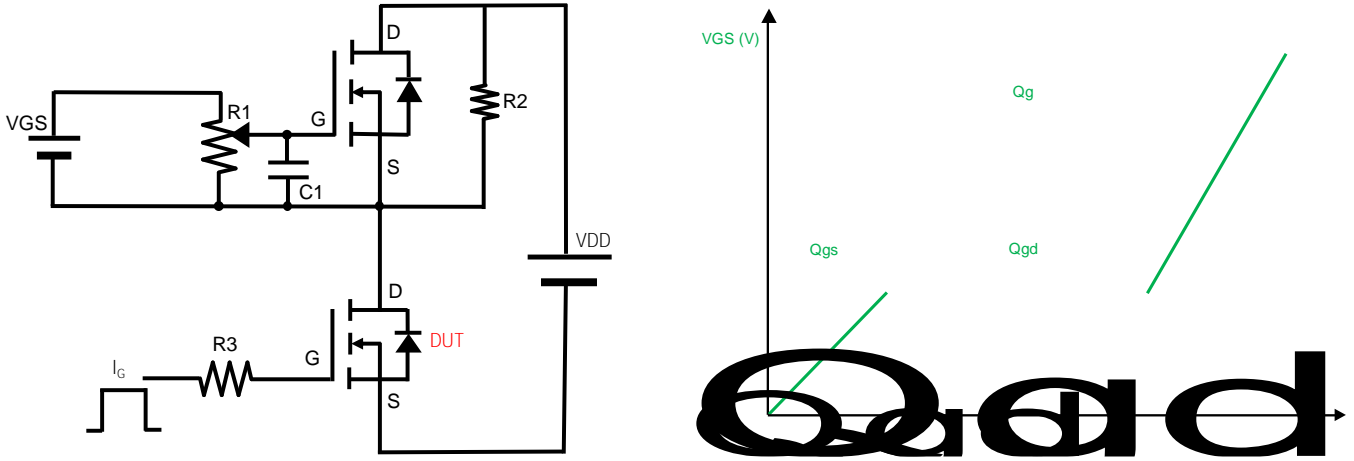


Figure B. Gate Charge Test Circuit & Waveform

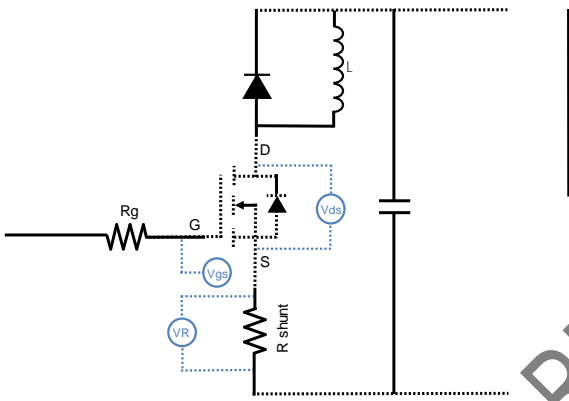


Figure C. Resistive Switching Test Circuit & Waveform

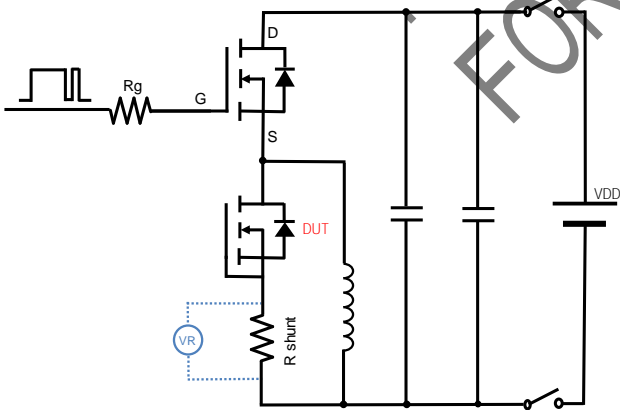
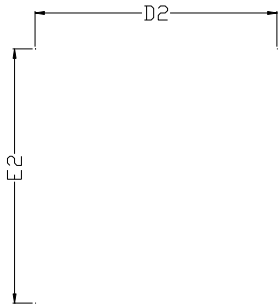


Figure D. Diode Recovery Test Circuit & Waveform



PDFN5060-8L-D-0.95MM Package information



Top View

Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.05	6.15
A	0.85	0.95	1.00
A1	0.203 BSC		
A2	0.08		
D1	4.25	4.35	4.45
E1	3.525	3.625	3.725
D2	5.20		
E2	5.55		
L1	0.4		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.10\text{mm}$.
3. The pad layout is for reference purposes only.

NOT RECOMMEND FOR NEW DESIGN



Disclaimer

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